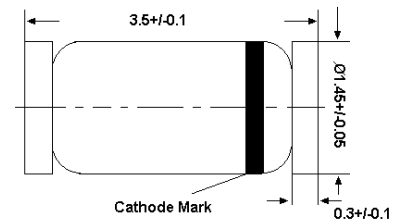


BAS81

Silicon Schottky Barrier Diodes

for general purpose applications

LL-34



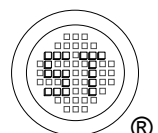
Glass case MiniMELF
Dimensions in mm

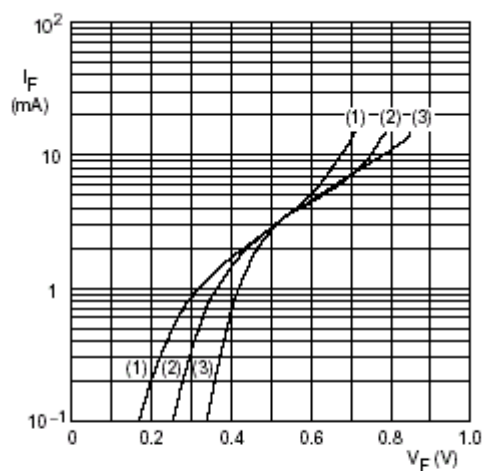
Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RRM}	40	V
Continuous Forward Current	I_F	30	mA
Repetitive Peak Forward Current $t_p \leq 1\text{ s}$, $\delta \leq 0.5$	I_{FRM}	150	mA
Repetitive Peak Forward Current $t_p = 1\text{ s}$	I_{FSM}	500	mA
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	320	K/W
Junction Temperature	T_j	125	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

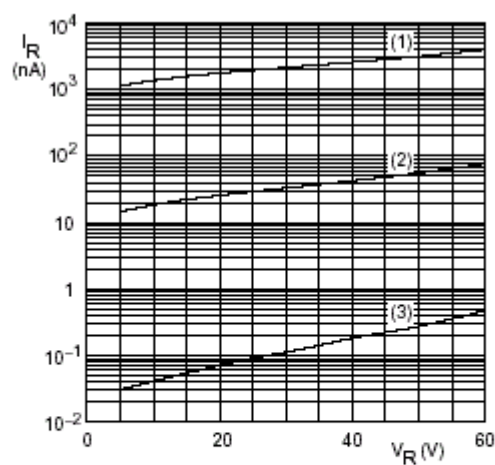
Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 0.1\text{ mA}$ at $I_F = 1\text{ mA}$ at $I_F = 15\text{ mA}$	V_F	0.33 0.41 1	V
Reverse Current at $V_R = 40$	I_R	200	nA
Total Capacitance at $V_R = 2\text{ V}$, $f = 1\text{ MHz}$	C_{tot}	1.6	pF





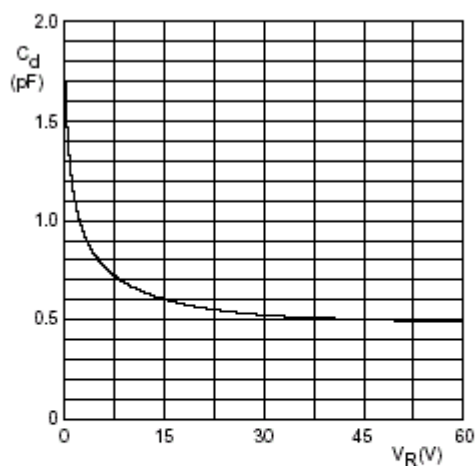
- (1) $T_{amb} = 85\text{ °C}$.
- (2) $T_{amb} = 25\text{ °C}$.
- (3) $T_{amb} = -40\text{ °C}$.

Forward current as a function of forward voltage; typical values.



- (1) $T_{amb} = 85\text{ °C}$.
- (2) $T_{amb} = 25\text{ °C}$.
- (3) $T_{amb} = -40\text{ °C}$.

Reverse current as a function of reverse voltage; typical values.



$f = 1\text{ MHz}$.

Diode capacitance as a function of reverse voltage; typical values.

